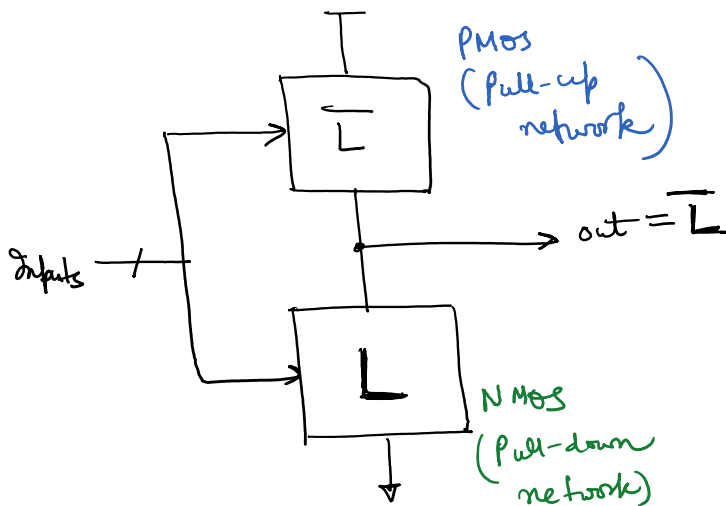
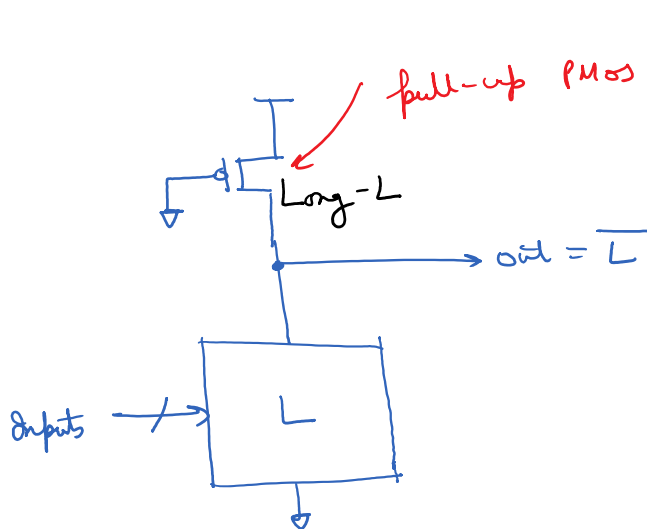


Static CMOS Logic:

* Input capacitance includes the NMOS & PMOS C_{in}
 ↳ large input capacitance and area

Ratiosed logic:

Long-length $\Rightarrow$ weaker pull-up or larger resistance

$$R_p = R_p' \frac{L}{W}$$

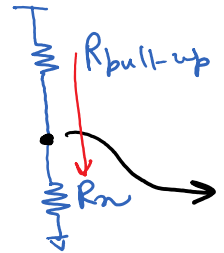
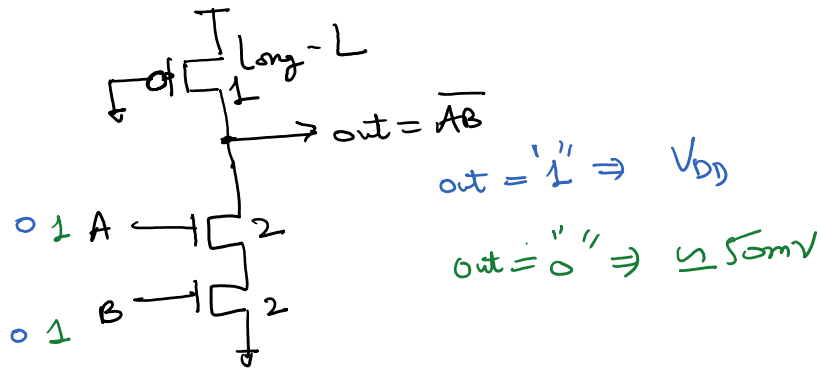
* reduces ^{net} input capacitance

* avoids large PMOS transistors

Called ratiosed logic as the voltage transfer curve depends

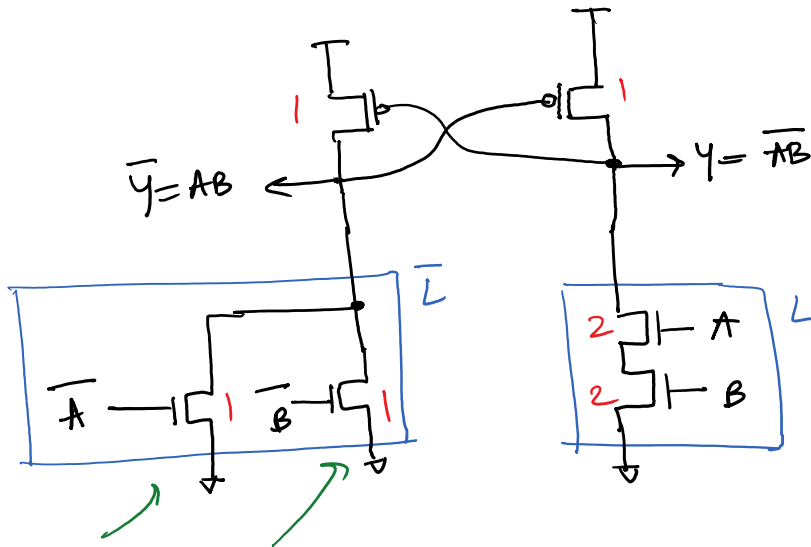
$$\text{upon } \frac{R_{\text{pull-up}}}{R_{\text{pull-down}}}$$

(-) Consumes static power ($V_{out,low} > 0$)
not full-swing



NAND

$$\overline{AB} = \overline{A} + \overline{B}$$



XOR / XNOR Gate

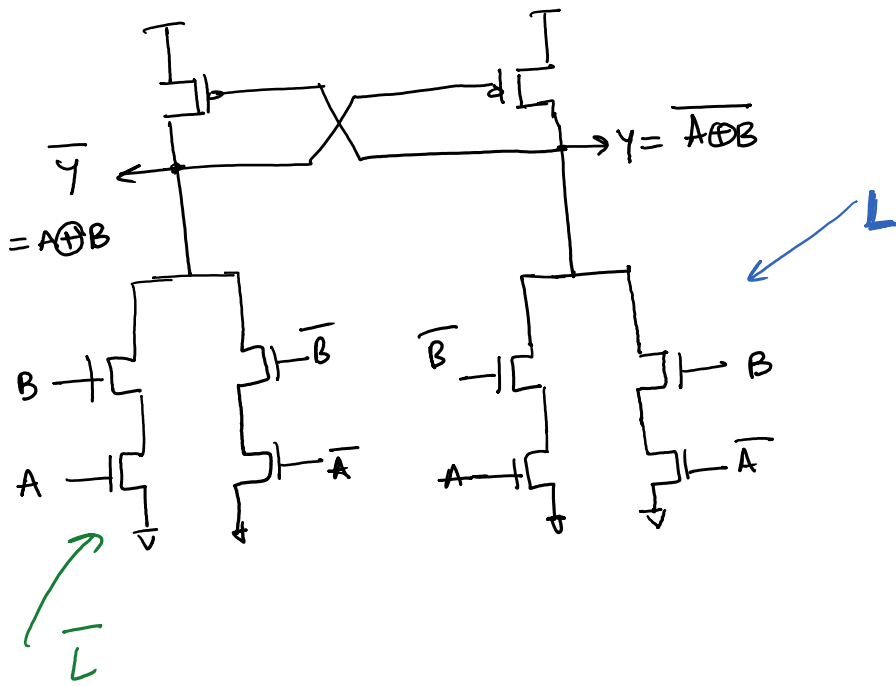
$$Y = \overline{A \oplus B} = \overline{L}$$

$$\Rightarrow L = \overline{A}B + A\overline{B} \quad \leftarrow L$$

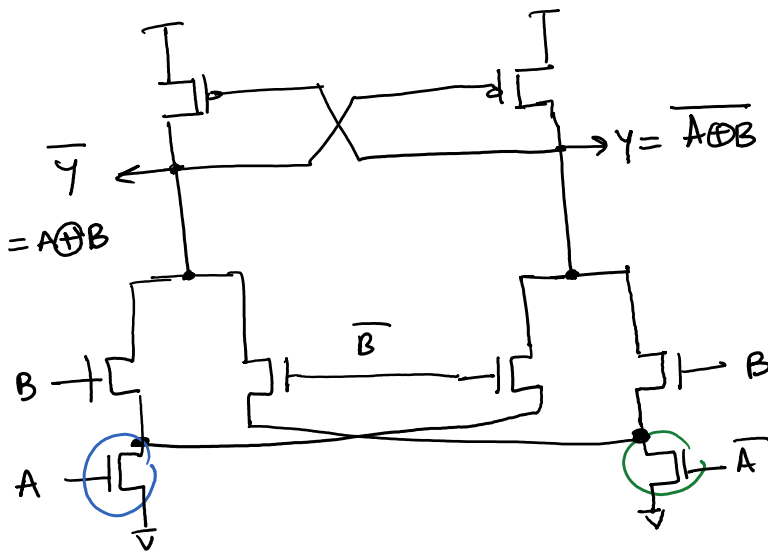
$$\overline{L} = AB + \overline{A}\overline{B}$$

T

T



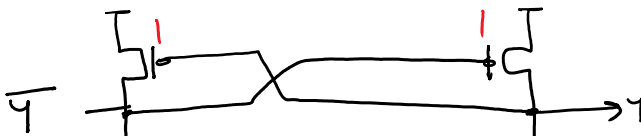
2-input XOR

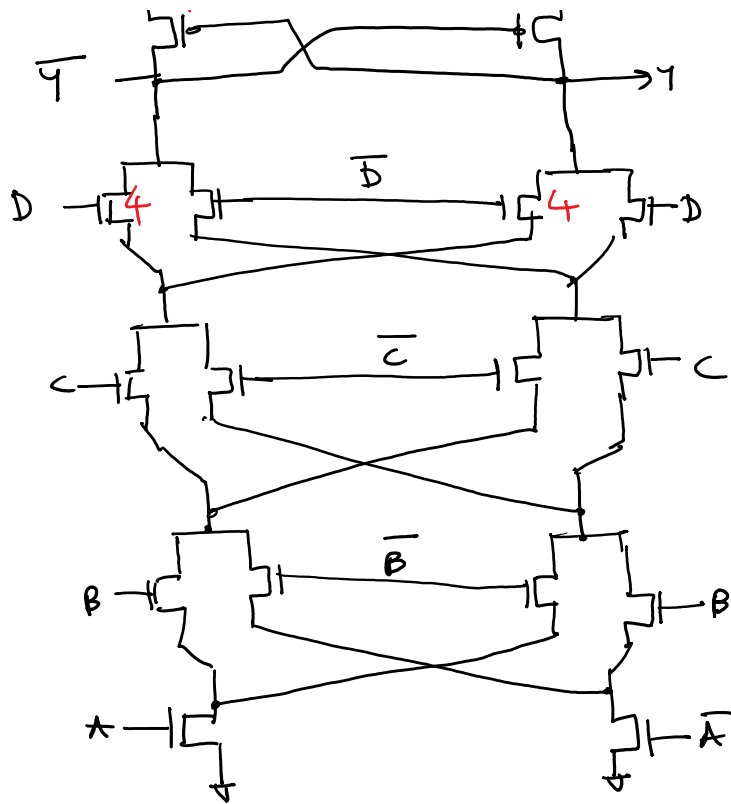


Eliminated duplication of
 $A \leftarrow \bar{A}$

* CMOS realizes compact XOR/XNOR logic

4-input XOR gate

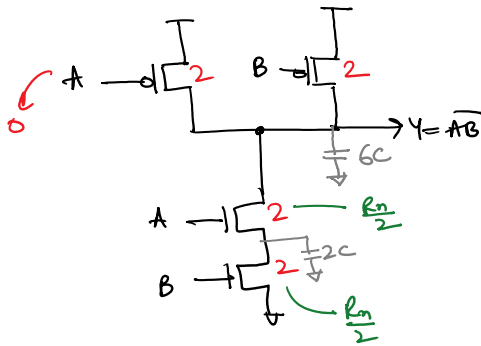




$$Y = \overline{A \oplus B \oplus C \oplus D}$$

Contamination & propagation Delays :

$$t_{pH2}, t_{pLH} \leftarrow t_{pd}$$



$$R_p = R_n = R$$

$AB \Rightarrow 01 \rightarrow 11$

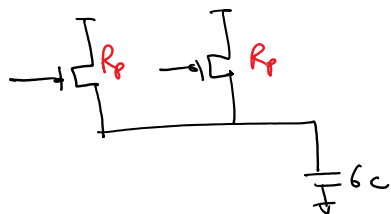
$$\text{delay} \Rightarrow \left(\frac{R_n}{2} + \frac{R_n}{2} \right) 6C = 6R_n C = 6RC$$

$AB \Rightarrow 11 \rightarrow 01$

$$\text{delay} \Rightarrow R_p \cdot 6C = 6R_p C = 6RC$$

$AB \Rightarrow 11 \rightarrow 00$

both MOS full-up.



$$\text{delay} = \frac{R_p}{2} \cdot 6C = 3RC$$

→ Not all input combinations lead to the same delay.

∴ $t_{pd} = \text{maximum delay from input to output}$

Contamination delay -
crossing 50% to the output

propagation delay (t_{pd}) = maximum time from input crossing
50% to the output crossing 50%.

